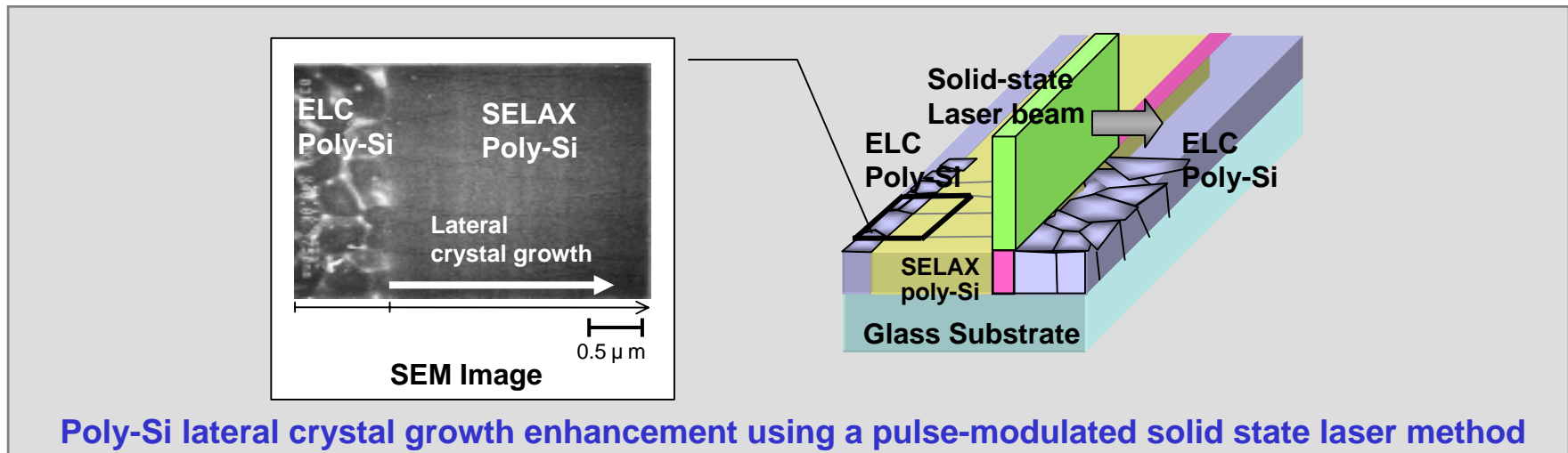


2002/5/16 Release

Development of low temperature poly-Si TFT formation technology for System-in-Display
- High field-effect mobility of 480 cm²/Vs and 1/4 reduction in threshold voltage deviation achieved -



Poly-Si lateral crystal growth enhancement using a pulse-modulated solid state laser method

A new technology for low temperature poly Si TFT (Thin Film Transistor) formation was developed for the next-generation display, "System-In-Display". The technology controls device characteristic variations to 1/4 of previous levels, and achieved a field-effect mobility of 480 cm²/Vs (max. 670 cm²/Vs). The technology developed, "Pulse-modulated Solid-State Laser Anneal Method", has high compatibility with conventional low temperature poly-silicon TFT processes, and can be further adapted for production on large glass panels.